



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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TECHNOLOGY CENTER 2800
#14/B
Q-27-2
Robertson
amdt

Applicants: INOUE et al.
Serial No.: 09/698,185
Filed: October 30, 2000
For: SEMICONDUCTOR DEVICE AND METHOD FOR
MANUFACTURING THE SAME
Group: 2827
Examiner: L. Thai

AMENDMENT

Assistant Commissioner
for Patents
Washington, D.C. 20231

September 13, 2002

Sir:

In response to the Office Action dated March 13, 2002, the period of response for which extension is requested by the attached Petition for Extension of Time, please amend the above-identified application as follows:

In the Specification: /

Page 74, paragraph beginning at line 4, has been rewritten as indicated below:

21 -- In the modified eighth step, a solder resist is applied onto the whole surface to form the surface protective film 6. Besides a spin coating method, a printing method using a mesh mask or a curtain coating method may be used as a method for applying the solder resist. To apply the solder resist, it is preferable that the wall surface of the dicing area of the stress relaxation layer 5 in the modified seventh step is not perpendicular to the wafer but V-shaped. This coating is performed after the